

	<h2>SI2308BDS-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI2308BDS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 60V 2.3A SOT23-3</p> <p>Datenblätter:  SI2308BDS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 103026 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2308BDS-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 60V 2.3A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	103026 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.09W (Ta), 1.66W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	2.3A (Tc)
Rds On (Max) @ Id, Vgs	156 mOhm @ 1.9A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	6.8nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	190pF @ 30V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)







SI2308BDS-T1-GE3 ist neu im Original, Suche SI2308BDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2308BDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2308BDS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2308BDS-T1-E3 Vishay / Siliconix MOSFET N-CH 60V 2.3A SOT23-3</p>	 <p>SI2308BDS-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 2.3A SOT23-3</p>	 <p>SI2308DS-T1-E3 Vishay / Siliconix MOSFET N-CH 60V 2A SOT23-3</p>	 <p>SI2308CDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 2.6A SOT23-3</p>
 <p>SI2308DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 2A SOT23-3</p>	 <p>SI2308ADS-T1-GE3 V V SOT23-3</p>	 <p>SI2308BDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 2.3A SOT23-3</p>	 <p>SI2308BDS VISHAY SI2308BDS VISHAY</p>

heiße Teile

Mehr

 SI2306CDS-T1-E3	 SI2306DS	 SI2306DS-T1	 SI2306DS-T1-E3	 SI2306DS-T1-GE3
 SI2306WCA	 SI2307BDS	 SI2307BDS-T1-E3	 SI2307BDS-T1-E3	 SI2307BDS-T1-GE3
 SI2307BDS-T1-GE3	 SI2307CDS	 SI2307CDS-T1-E3	 SI2307CDS-T1-E3	 SI2307CDS-T1-GE3
 SI2307CDS-T1-GE3	 SI2307DS	 SI2307DS-T1	 SI2307DS-T1-E3	 SI2307DS-T1-GE3
 SI2307DS-T7-E3	 SI2308BDS	 SI2308BDS-T1-E3	 SI2308BDS-T1-E3	 SI2308BDS-T1-GE3
 SI2308DS	 SI2308DS-T1	 SI2308DS-T1-E3	 SI2308DS-T1-E3	 SI2308DS-T1-GE3
 SI2309BDS-T1-E3	 SI2309BDS-T1-GE3	 SI2309CDS-T1-GE3	 SI2309CDS-T1-GE3	 SI2309DS
 SI2309DS-T1	 SI2309DS-T1-E3	 SI2309DS-T1-E3	 SI2309DS-T1-GE3	 SI2309DS-TI-E3
 SI2309DS/A92T	 SI2310DS	 SI2310DS-T1-E3	 SI2310DS-T1-GE3	 SI2311DS
 SI2311DS-T1	 SI2311DS-T1-E3	 SI2311DS-T1-E3	 SI2311DS-T1-GE3	 SI2311DS-T1-GE3

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